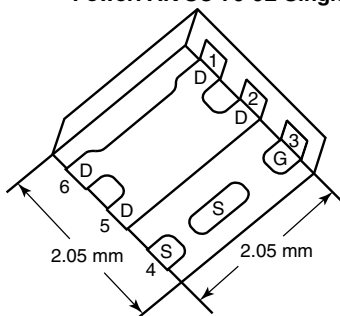


P-Channel 12-V (D-S) MOSFET

PRODUCT SUMMARY

V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)	Q _g (Typ.)
- 12	0.029 at V _{GS} = - 4.5 V	- 12 ^a	23 nC
	0.034 at V _{GS} = - 2.5 V	- 12 ^a	
	0.044 at V _{GS} = - 1.8 V	- 12 ^a	
	0.100 at V _{GS} = - 1.5 V	- 3	

PowerPAK SC-70-6L-Single



Ordering Information:

SiA413DJ-T4-GE3 (Lead (Pb)-free and Halogen-free)

SiA413DJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- TrenchFET® Power MOSFET
- New Thermally Enhanced PowerPAK® SC-70 Package
 - Small Footprint Area
 - Low On-Resistance
- Material categorization:
For definitions of compliance please see www.vishay.com/doc?99912

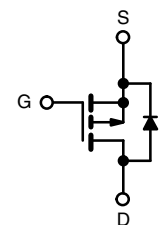
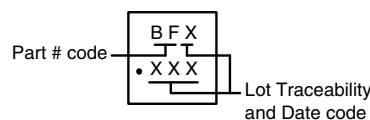


RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Load Switch, PA Switch and Battery Switch for Portable Devices

Marking Code



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	- 12	V
Gate-Source Voltage	V _{GS}	± 8	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C - 12 ^a	A
		T _C = 70 °C - 12 ^a	
		T _A = 25 °C - 10 ^{b, c}	
		T _A = 70 °C - 8 ^{b, c}	
Pulsed Drain Current	I _{DM}	- 40	
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C - 12 ^a	
		T _A = 25 °C - 2.9 ^{b, c}	
Maximum Power Dissipation	P _D	T _C = 25 °C 19	W
		T _C = 70 °C 12	
		T _A = 25 °C 3.5 ^{b, c}	
		T _A = 70 °C 2.2 ^{b, c}	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, f}	R _{thJA}	28	36	°C/W
Maximum Junction-to-Case (Drain)	R _{thJC}	5.3	6.5	

Notes:

- Package limited.
- Surface mounted on 1" x 1" FR4 board.
- t = 5 s.
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is 80 °C/W.

SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 12			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = - 250 μA		- 11		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			2.7		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 0.4		- 1	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 8 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 12 V, V _{GS} = 0 V			- 1	μA
		V _{DS} = - 12 V, V _{GS} = 0 V, T _J = 55 °C			- 10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≤ - 5 V, V _{GS} = - 4.5 V	- 20			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 6.7 A		0.024	0.029	Ω
		V _{GS} = - 2.5 V, I _D = - 6.2 A		0.028	0.034	
		V _{GS} = - 1.8 V, I _D = - 2.3 A		0.036	0.044	
		V _{GS} = - 1.5 V, I _D = - 1 A		0.050	0.100	
Forward Transconductance ^a	g _{fs}	V _{DS} = - 10 V, I _D = - 6.7 A		30		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = - 10 V, V _{GS} = 0 V, f = 1 MHz		1800		pF
Output Capacitance	C _{oss}			450		
Reverse Transfer Capacitance	C _{rss}			390		
Total Gate Charge	Q _g	V _{DS} = - 6 V, V _{GS} = - 8 V, I _D = - 10 A		38	57	nC
		V _{DS} = - 6 V, V _{GS} = - 4.5 V, I _D = - 10 A		23	35	
Gate-Source Charge	Q _{gs}			3		
Gate-Drain Charge	Q _{gd}			6.5		
Gate Resistance	R _g	f = 1 MHz		7		Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 6 V, R _L = 0.75 Ω I _D ≅ - 8 A, V _{GEN} = - 4.5 V, R _g = 1 Ω		20	30	ns
Rise Time	t _r			40	60	
Turn-Off Delay Time	t _{d(off)}			65	100	
Fall Time	t _f			40	60	
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 6 V, R _L = 0.75 Ω I _D ≅ - 8 A, V _{GEN} = - 8 V, R _g = 1 Ω		10	15	
Rise Time	t _r			12	20	
Turn-Off Delay Time	t _{d(off)}			70	105	
Fall Time	t _f			40	60	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 12	A
Pulse Diode Forward Current	I _{SM}				40	
Body Diode Voltage	V _{SD}	I _S = - 8 A, V _{GS} = 0 V		- 0.8	- 1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = - 8 A, di/dt = 100 A/μs, T _J = 25 °C		40	60	ns
Body Diode Reverse Recovery Charge	Q _{rr}			20	30	nC
Reverse Recovery Fall Time	t _a			14		ns
Reverse Recovery Rise Time	t _b			26		

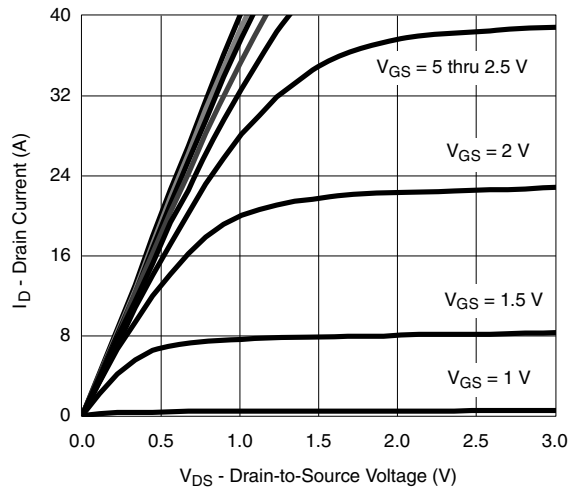
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

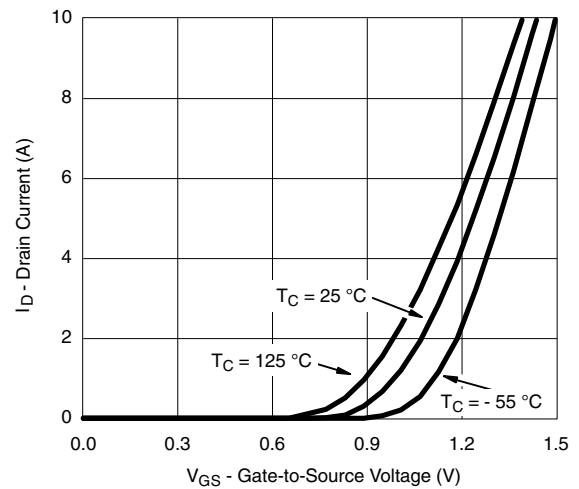
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

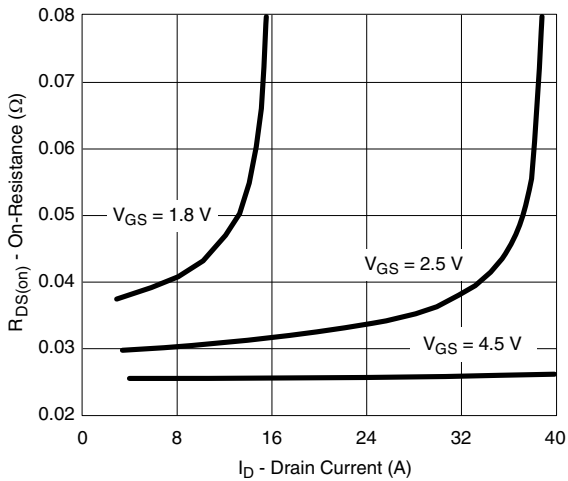
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



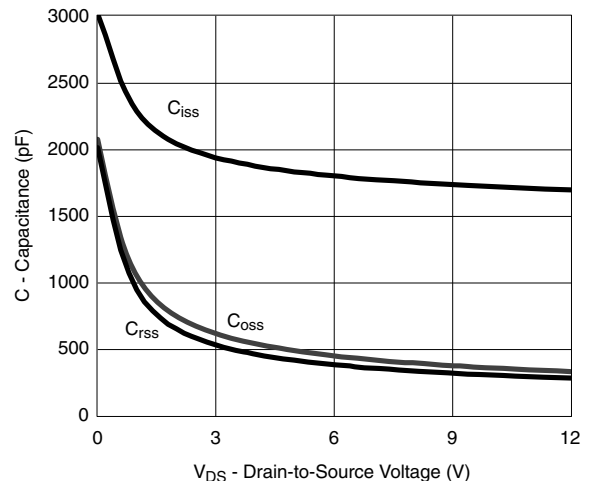
Output Characteristics



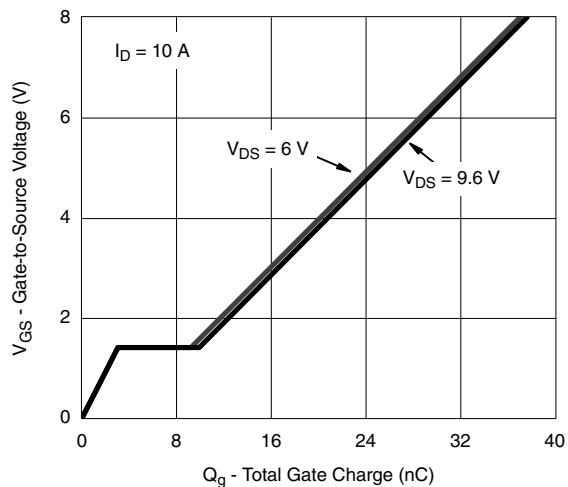
Transfer Characteristics



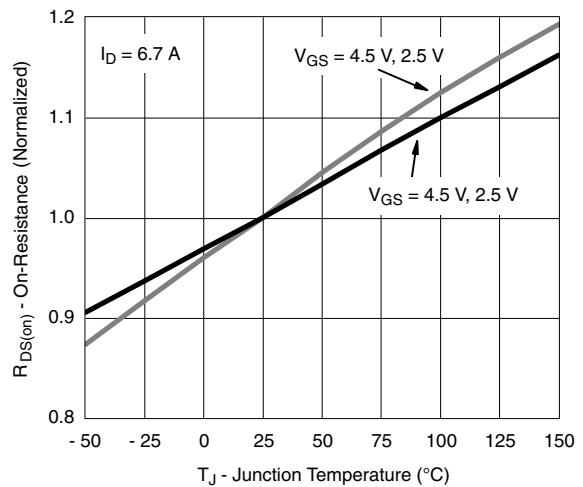
On-Resistance vs. Drain Current and Gate Voltage



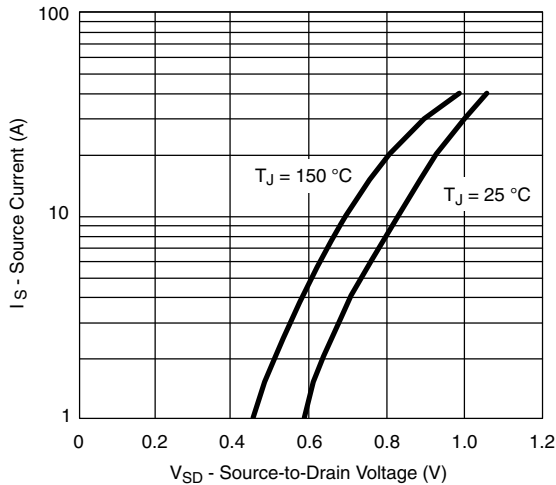
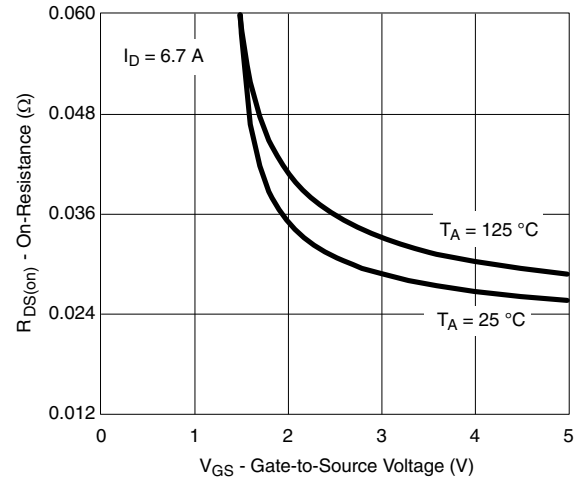
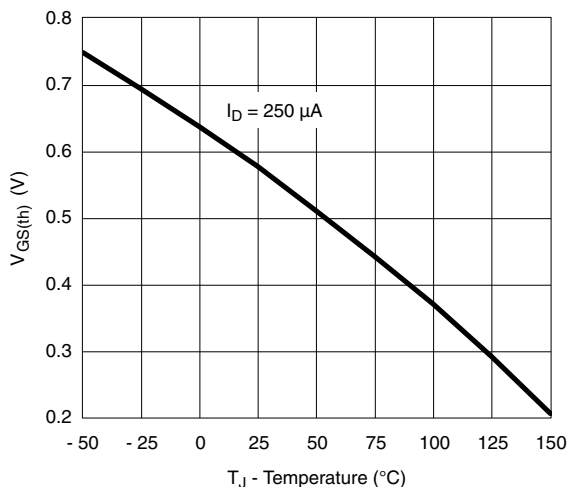
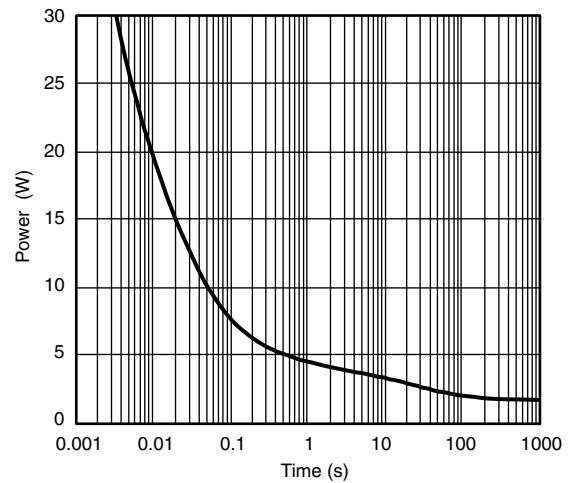
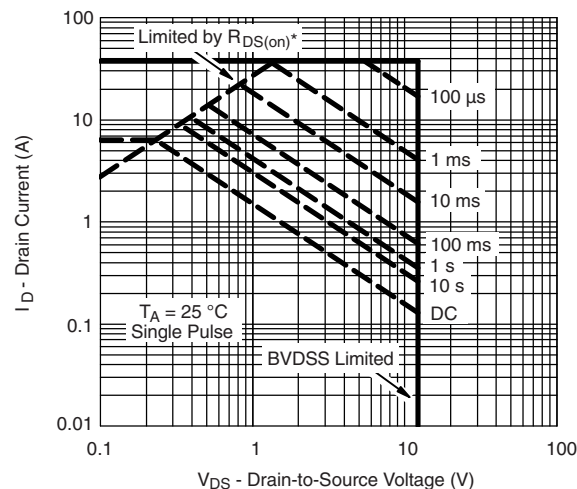
Capacitance



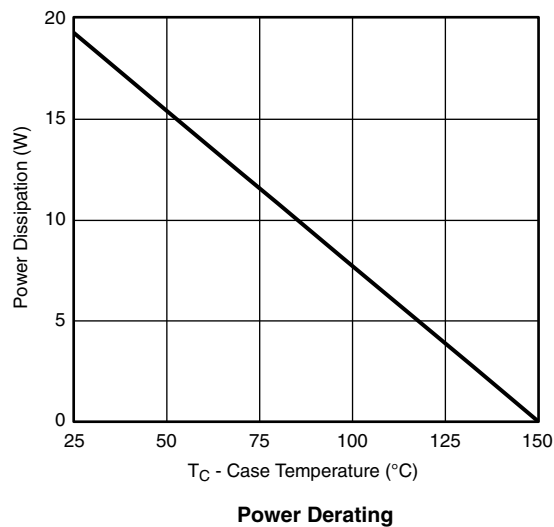
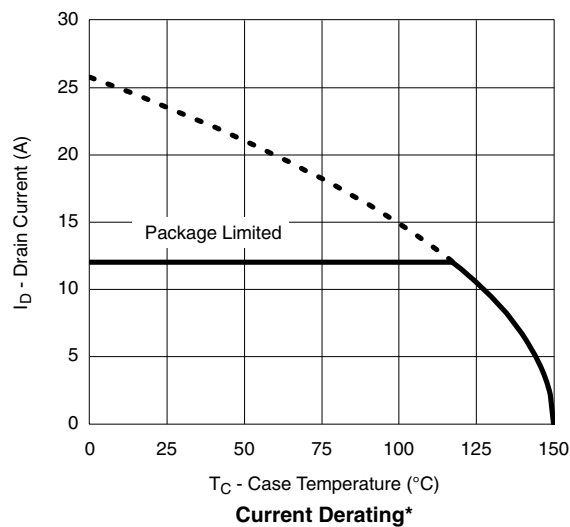
Gate Charge



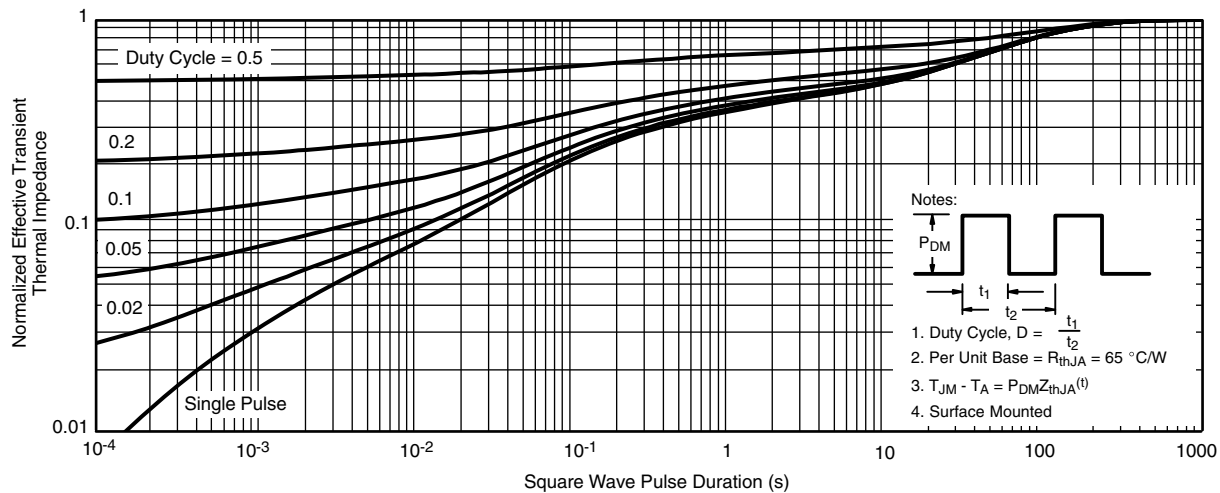
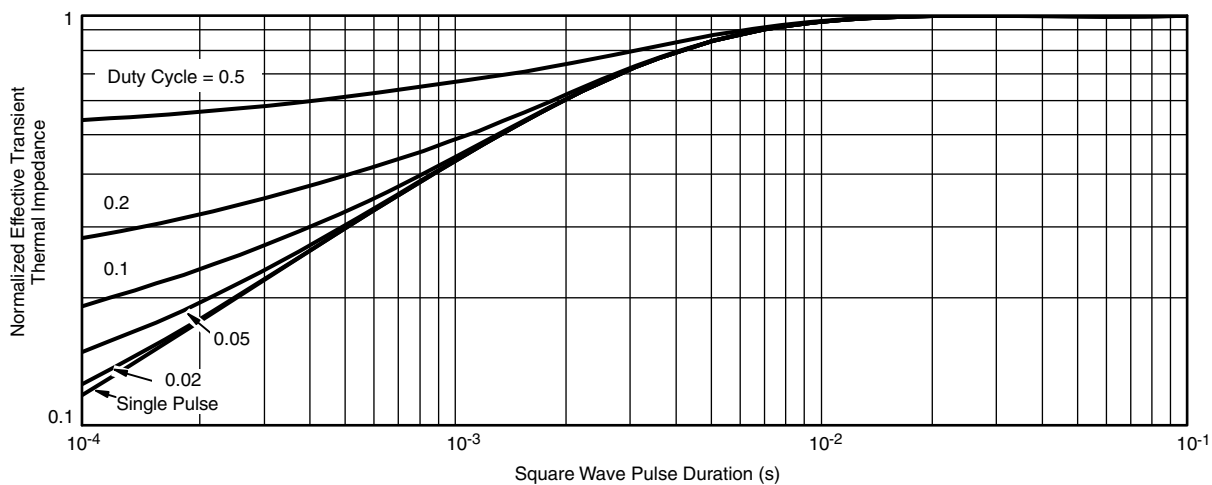
On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power, Junction-to-Ambient****Safe Operating Area, Junction-to-Ambient**

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



* The power dissipation P_D is based on $T_{J(max.)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Case**

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